NX3DV642

3-lane high-speed MIPI compatible switch

Rev. 1 — 20 August 2012 Product data sheet

1. General description

The NX3DV642 is a high-speed triple-pole double-throw differential signal switch. The device is optimized for switching between two MIPI devices, such as cameras or LCD displays and on-board multimedia application processors.

The NX3DV642 is compatible with the requirements of Mobile Industry Processor Interface (MIPI). The low capacitance design allows the NX3DV642 to switch signals that exceed 500 MHz in frequency

2. Features and benefits

- Supply voltage range from 2.65 V to 4.3 V
- 7.5 Ω typical ON resistance
- 8.4 pF typical ON capacitance
- 950 MHz typical bandwidth or data frequency
- Low crosstalk of −55 dB at 100 MHz
- Break-before-make switching
- ESD protection:
  - HBM JESD22-A114F Class 2 exceeds 2000 V
  - CDM AEC-Q100-011 revision B exceeds 1000 V
  - HBM exceeds 12000 V for power to GND protection
- Latch-up performance exceeds 100 mA per JESD 78 Class II Level A
- Specified from −40 °C to +85 °C

3. Applications

- Dual camera applications for cell phones
- Dual LCD applications for cell phones, digital camera displays and viewfinders

4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
NX3DV642GU	−40 °C to +85 °C	XQFN24	plastic, extremely thin quad flat package; no leads; 24 terminals; body 2.5 x 3.4 x 0.5 mm	SOT1310-1

5. Marking

Table 2. Marking

Type number	Marking code
NX3DV642GU	3DV642

6. Functional diagram

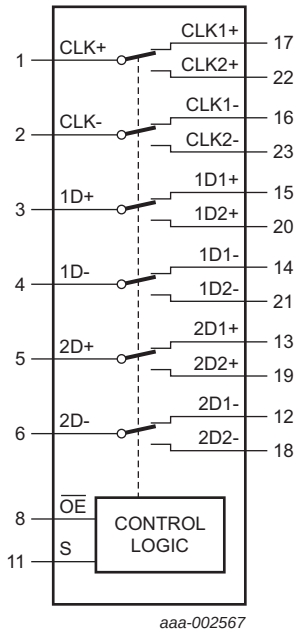


Fig 1. Logic symbol

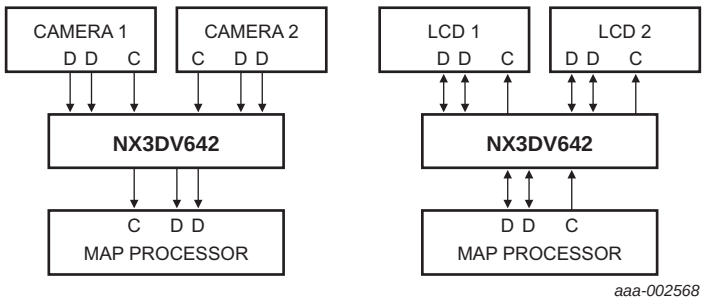


Fig 2. Application block diagram

7. Pinning information

7.1 Pinning

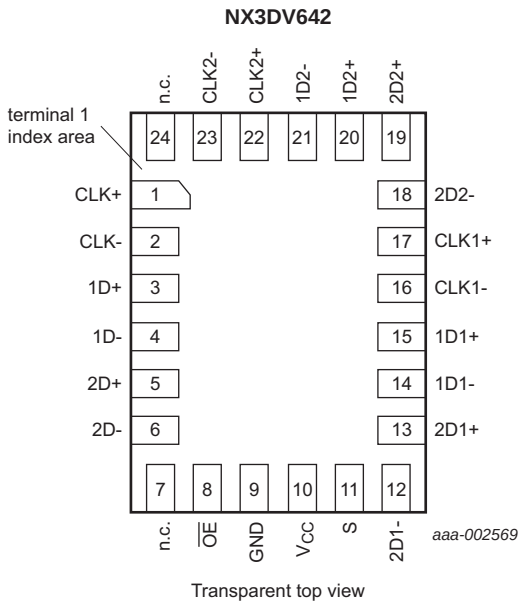


Fig 3. Pin configuration SOT1310-1 (XQFN24)

7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
CLK+, CLK–	1, 2	common output or input clock path
1D+, 1D–	3, 4	common output or input data path 1D
2D+, 2D–	5, 6	common output or input data path 2D
n.c.	7, 24	not connected
$\overline{OE}$	8	output enable input (active LOW)
GND	9	ground (0 V)
V_{CC}	10	supply voltage
S	11	select input
2D1+, 2D1–	13, 12	independent input or output data path 2D1
1D1+, 1D1–	15, 14	independent input or output data path 1D1
CLK1+, CLK1–	17, 16	independent input or output clock path CLK1
2D2+, 2D2–	19, 18	independent input or output data path 2D2
1D2+, 1D2–	20, 21	independent input or output data path 1D2
CLK2+, CLK2–	22, 23	independent input or output clock path CLK2

8. Functional description

Table 4. Function table[1]

Input		Channel on
S	**$\overline{OE}$**	
L	L	CLKn, 1Dn, 2Dn = CLK1n, 1D1n, 2D1n
H	L	CLKn, 1Dn, 2Dn = CLK2n, 1D2n, 2D2n
X	H	switch off

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care. (n = + or –)

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+5.5	V
V_I	input voltage	pins S and $\overline{OE}$	[1]	–0.5	+5.5	V
V_{SW}	switch voltage			–0.5	+5.5	V
I_{IK}	input clamping current	V_I < –0.5 V		–50	-	mA
I_{SK}	switch clamping current	V_I < –0.5 V		–50	+50	mA
I_{SW}	switch current			–100	+100	mA
I_{CC}	supply current			-	+50	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +85 °C		-	533	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

10. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			2.65	4.3	V
V_I	input voltage	pins S and $\overline{OE}$		0	4.3	V
V_{SW}	switch voltage		[1]	0	4.5	V
T_{amb}	ambient temperature			–40	+85	°C

[1] To avoid sinking GND current from terminals CLKn, 1Dn and 2Dn when switch current flows in terminals CLK1n, CLK2n, 1D1n 1D2n, 2D1n and 2D2n (n = + or –), the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminals CLKn, 1Dn and 2Dn, no GND current flows from terminals CLK1n, CLK2n, 1D1n 1D2n, 2D1n and 2D2n. In this case, there is no limit for the voltage drop across the switch.

11. Static characteristics

Table 7. Static characteristics

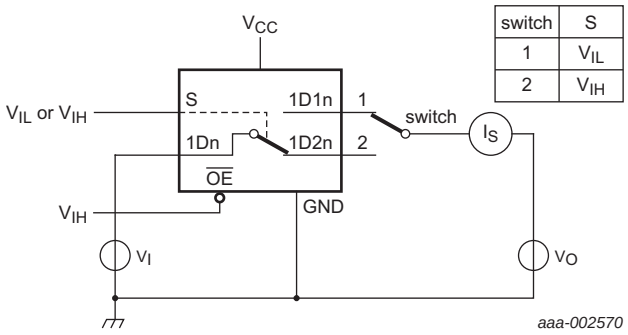
At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions		T_{amb} = –40 °C to +85 °C			Unit
				Min	Typ[1]	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 2.65 V to 2.775 V		1.3	-	-	V
		V_{CC} = 4.3 V		1.7	-	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.65 V to 2.775 V		-	-	0.5	V
		V_{CC} = 4.3 V		-	-	0.7	V
V_{IK}	input clamping voltage	V_{CC} = 2.775 V; I_I = –18 mA		–1.2	-	-	V
I_I	input leakage current	pins S and $\overline{OE}$; V_I = GND to 4.3 V; V_{CC} = 4.3 V		-	-	±1	µA
$I_{S(OFF)}$	OFF-state leakage current	V_{CC} = 4.3 V; see Figure 4		-	-	±2	µA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 4.3 V; V_{CC} = 0 V		-	-	±2	µA
I_{CC}	supply current	V_I = V_{CC} or GND; V_{SW} = GND or V_{CC}; V_{CC} = 4.3 V		-	-	2	µA
ΔI_{CC}	additional supply current	V_I = 1.8 V; V_{SW} = GND or V_{CC}; V_{CC} = 2.775 V		-	-	1.5	µA
C_I	input capacitance	pins S and OE		-	1.3	-	pF
$C_{S(OFF)}$	OFF-state capacitance	pins CLK1n, CLK2n, 1D1n 1D2n, 2D1n and 2D2n; V_I = 0 V to 3.3 V	[2]	-	3.0	-	pF
$C_{S(ON)}$	ON-state capacitance	pins CLKn, 1Dn and 2Dn; V_I = 0 V to 3.3 V	[2]	-	8.4	-	pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 2.775 V.

[2] n = + or –.

11.1 Test circuits



V_I = V_{CC} or GND and V_O = GND or V_{CC}.

Test circuit also applies for 2Dn, 2D1n, 2D2n CLKn, CLK1n and CLK2n (n = + or –).

Fig 4. Test circuit for measuring OFF-state leakage current

11.2 ON resistance

Table 8. ON resistance

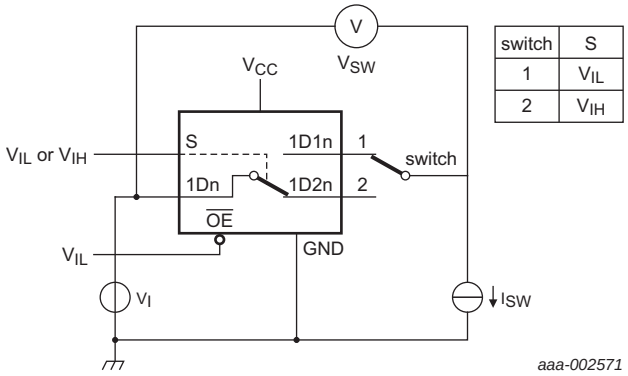
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		–40 °C to +85 °C			Unit
				Min	Typ[1]	Max	
low speed mode							
R_{ON}	ON resistance	V_I = 1.2 V; I_{SW} = 10 mA; see Figure 5					
		V_{CC} = 2.65 V		-	7.5	14	Ω
ΔR_{ON}	ON resistance mismatch between channels	V_I = 1.2 V; I_{SW} = 10 mA	[2]				
		V_{CC} = 2.65 V		-	0.65	-	Ω
High speed mode							
R_{ON}	ON resistance	V_I = 0.1 V; I_{SW} = 10 mA; see Figure 5					
		V_{CC} = 2.65 V		-	5.5	9.5	Ω
ΔR_{ON}	ON resistance mismatch between channels	V_I = 0.1 V; I_{SW} = 10 mA	[2]				
		V_{CC} = 2.65 V		-	0.65	-	Ω

[1] Typical values are measured at T_{amb} = 25 °C.

[2] Measured at identical V_{CC}, temperature and input voltage.

11.3 ON resistance test circuit and graphs



switch	S
1	V_{IL}
2	V_{IH}

$R_{ON} = V_{SW} / I_{SW}$.

Test circuit also applies for 2Dn, 2D1n, 2D2n CLKn, CLK1n and CLK2n (n = + or –).

Fig 5. Test circuit for measuring ON resistance

12. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see Figure 9.

Symbol	Parameter	Conditions		T_{amb} = –40 °C to +85 °C			Unit
				Min	Typ[1]	Max	
t_{pd}	propagation delay	CLKn to CLK1n or CLK2n; 1Dn to 1D1n or 1D2n or 2Dn to 2D1n or 2D2n; see Figure 6	[2][3][4]				
		V_{CC} = 2.775 V		-	0.25	-	ns
t_{en}	enable time	S or $\overline{OE}$ to CLKn, 1Dn or 2Dn; see Figure 7	[2][3]				
		V_{CC} = 2.65 V to 2.775 V		-	13.5	37	ns
t_{dis}	disable time	S or $\overline{OE}$ to CLKn, 1Dn or 2Dn; see Figure 7	[2][3]				
		V_{CC} = 2.65 V to 2.775 V		-	5.5	27	ns
t_{b-m}	break-before-make time	see Figure 8	[4]				
		V_{CC} = 2.65 V to 2.775 V		3	7	-	ns
$t_{sk(p)}$	pulse skew time	V_{CC} = 2.65 V to 2.775 V; V_{SW} = 0.2 V (p-p)	[4]	-	10	-	ps
$t_{sk(o)}$	output skew time	V_{CC} = 2.65 V to 2.775 V; V_{SW} = 0.2 V (p-p)	[4]	-	15	-	ps
$t_{sk(pr)}$	process skew time	V_{CC} = 2.65 V to 2.775 V; V_{SW} = 0.2 V (p-p)	[4]	-	40	-	ps

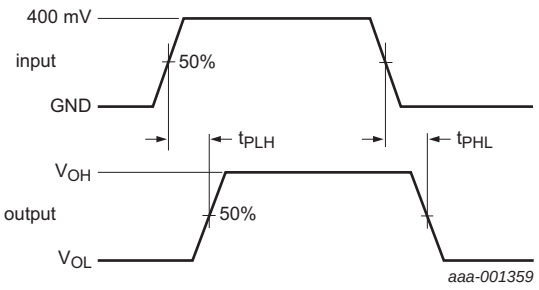
[1] Typical values are measured at T_{amb} = 25 °C, C_L = 5 pF and V_{CC} = 2.775 V.

[2] n = + or –.

[3] t_{pd} is the same as t_{PLH} and t_{PHL}.
t_{en} is the same as t_{PZH}
t_{dis} is the same as t_{PHZ}

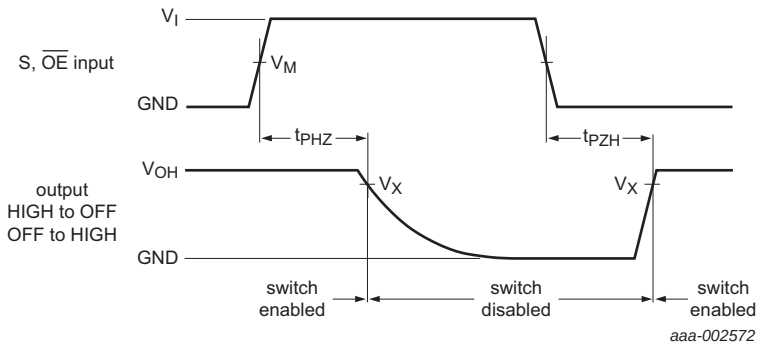
[4] Guaranteed by design.

12.1 Waveform and test circuits



Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.
$t_r = t_f \leq 500$ ps.

Fig 6. The data input to output propagation delay times



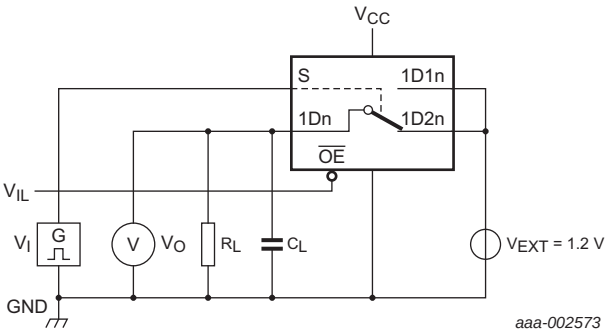
Measurement points are given in Table 10.

Logic level: V_{OH} and V_{OL} are typical output voltage levels that occur with the output load.

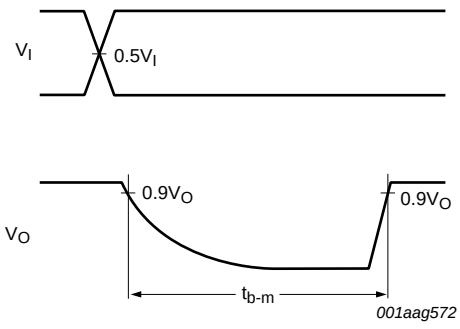
Fig 7. Enable and disable times

Table 10. Measurement points

Supply voltage	Input		Output
V_{CC}	V_M	V_I	V_X
2.65 V to 2.775 V	$0.5V_{CC}$	V_{CC}	$0.9V_{OH}$



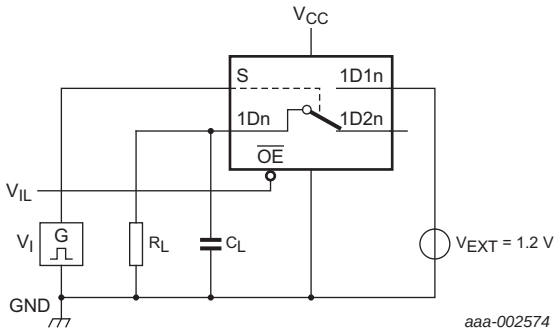
a. Test circuit.



b. Input and output measurement points

Test circuit also applies for 2Dn, 2D1n, 2D2n CLKn, CLK1n and CLK2n (n = + or −).

Fig 8. Test circuit for measuring break-before-make timing



Test circuit also applies for 2Dn, 2D1n, 2D2n CLKn, CLK1n and CLK2n (n = + or –).

Test data is given in Table 11.

Definitions test circuit:

R_T = Termination resistance (should be equal to output impedance Z_o of the pulse generator).

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

V_{EXT} = External voltage for measuring switching times.

V_I may be connected to S or $\overline{OE}$.

Fig 9. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Input		Load	
V_{CC}	V_I	t_r, t_f	C_L	R_L
2.65 V to 2.775 V	V_{CC}	≤ 2.5 ns	5 pF	50 Ω

12.2 Additional dynamic characteristics

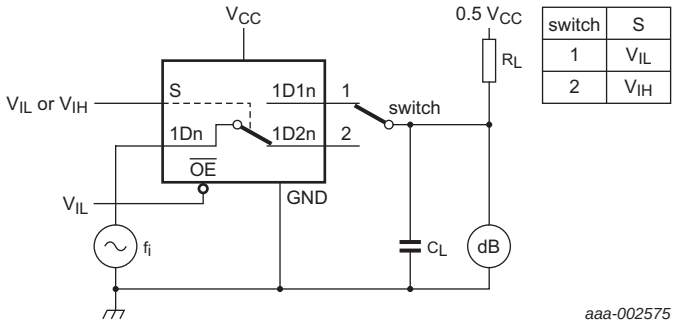
Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); V_I = GND or V_{CC} (unless otherwise specified); $t_r = t_f \leq 2.5$ ns.

Symbol	Parameter	Conditions		T_{amb} = 25 °C			Unit
				Min	Typ	Max	
$f_{(-3dB)}$	–3 dB frequency response	R_L = 50 Ω; see Figure 10	[1]				
		C_L = 0 pF; V_{CC} = 2.775 V		-	950	-	MHz
α_{iso}	isolation (OFF-state)	f_i = 100 MHz; R_L = 50 Ω; see Figure 11	[1]				
		V_{CC} = 2.775 V		-	–35	-	dB
Xtalk	crosstalk	between switches; f_i = 100 MHz; R_L = 50 Ω; see Figure 12	[1]				
		V_{CC} = 2.775 V		-	–55	-	dB

[1] f_i is biased at $0.5V_{CC}$.

12.3 Test circuits

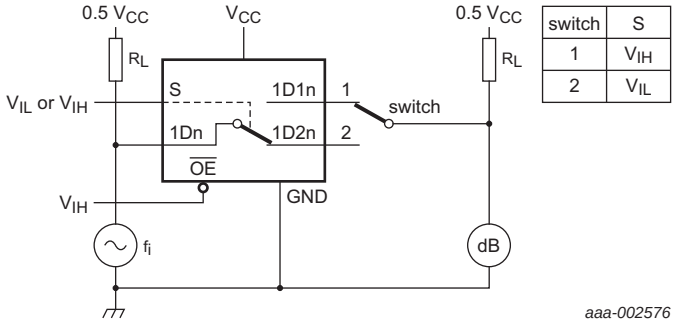


switch	S
1	V_{IL}
2	V_{IH}

Adjust f_i voltage to obtain 0 dBm level at output. Increase f_i frequency until dB meter reads −3 dB.

Test circuit also applies for 2Dn, 2D1n, 2D2n CLKn, CLK1n and CLK2n (n = + or −).

Fig 10. Test circuit for measuring the frequency response when channel is in ON-state

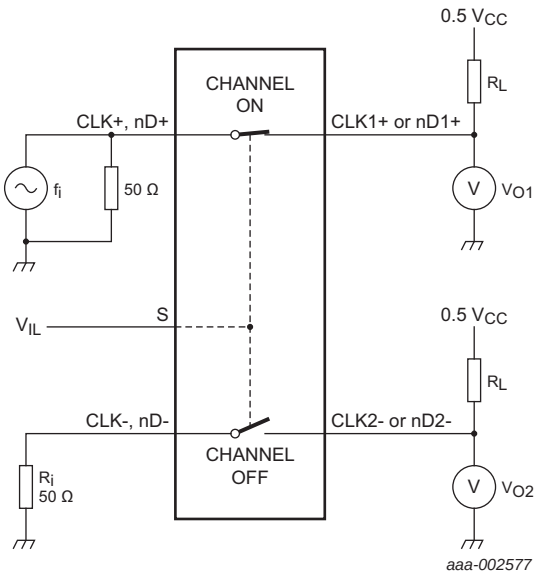


switch	S
1	V_{IH}
2	V_{IL}

Adjust f_i voltage to obtain 0 dBm level at input.

Test circuit also applies for 2Dn, 2D1n, 2D2n CLKn, CLK1n and CLK2n (n = + or −).

Fig 11. Test circuit for measuring isolation (OFF-state)

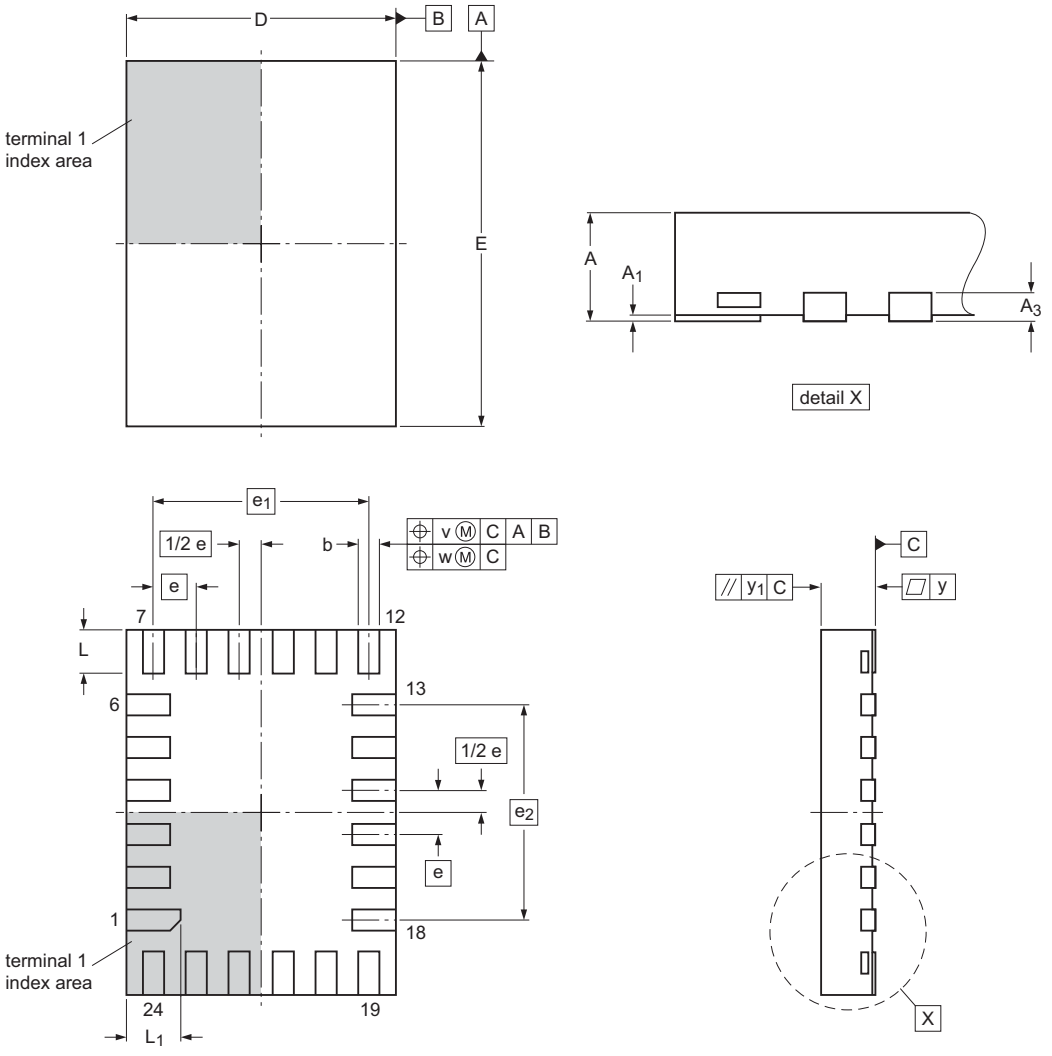


$20 \log_{10} (V_{O2} / V_{O1})$ or $20 \log_{10} (V_{O1} / V_{O2})$.

Fig 12. Test circuit for measuring crosstalk between switches

13. Package outline

XQFN24: plastic, extremely thin quad flat package; no leads; 24 terminals; body 2.5 x 3.4 x 0.5 mm **SOT1310-1**



Dimensions

Unit		A	A_1	b	A_3	D	E	e	e_1	e_2	L	L_1	v	w	y	y_1
mm	max	0.5	0.05	0.25		2.6	3.5				0.45	0.55				
	nom			0.20	0.127	2.5	3.4	0.4	2.0	2.0	0.40	0.50	0.10	0.05	0.05	0.05
	min		0.00	0.15		2.4	3.3				0.35	0.45				

Note
1. Plastic or metal protrusions of 0.075 mm maximum per side are not included

sot1310-1_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1310-1		MO-288				~~11-07-19~~ 11-08-18

Fig 13. Package outline SOT1310-1 (XQFN24)

14. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3DV642 v.1	20120820	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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18. Contents

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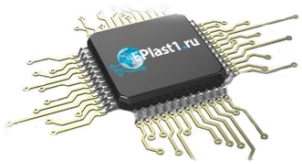
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)
Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.